IN THE SPECIFICATION

Following is a marked-up version of each amended paragraph of the subject patent application. The Examiner is requested to delete the indicated paragraph and replace it with the amended paragraph. The location for each of the deleted and replaced paragraphs is indicated.

The paragraph immediately above the heading "FIELD OF THE INVENTION" on line 5 of page 1, should be amended as follows:

"This application claims the benefit of issued Patent No. 6,690,040 ~~Application No. 09/950,384~~ filed on September 10, 2001."

The paragraph beginning at line 24 on page 5, and ending at line 2 on page 6, should be amended as follows:

An etch stop, as is known to those skilled in the art, is designed to prevent an etch from proceeding to an underlying or overlaying layer or layers. The etch stop therefore, has a significantly greater etch resistance to a selected etchant than the adjacent layer or layers to be etched. Specifically in this case, for the selected etchant, the etch rate of the etch stop layer (or offset spacer) 211 is much slower than the etch rate of the overlying layer, which, as will be discussed below, is a sacrificial layer. According to the present invention, for removal of a sacrificial layer of silicon oxide (e.g., silicon oxide formed from tetraethylene ortho silicate (TEOS)), an appropriate etch stop material limits action of the etchant on the underlying layer.

The paragraph beginning at line 1 on page 7, and ending at line 3 on page 7, should be amended as follows:

An etch stop layer (or offset spacer) 216 is also formed over the sacrificial layer 215. The etch stop layer 216 serves a similar function as the layer 211 and may, for example, be silicon nitride.